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## **Possibilities of Presence of SCHLOGL Quasichemical Reactions in an Atmosphere of Own Silicon Defects**

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Within the limits of debatable discussion the important case of evolution of an atmosphere of own dot defects of silicon is considered. It is shown, that own interstitial atoms of silicon and to concentration of vacancies in an atmosphere of own defects of silicon presence by stable states is probably inherent in concentration, transition between which can be described Schlogl quasichemical reactions.